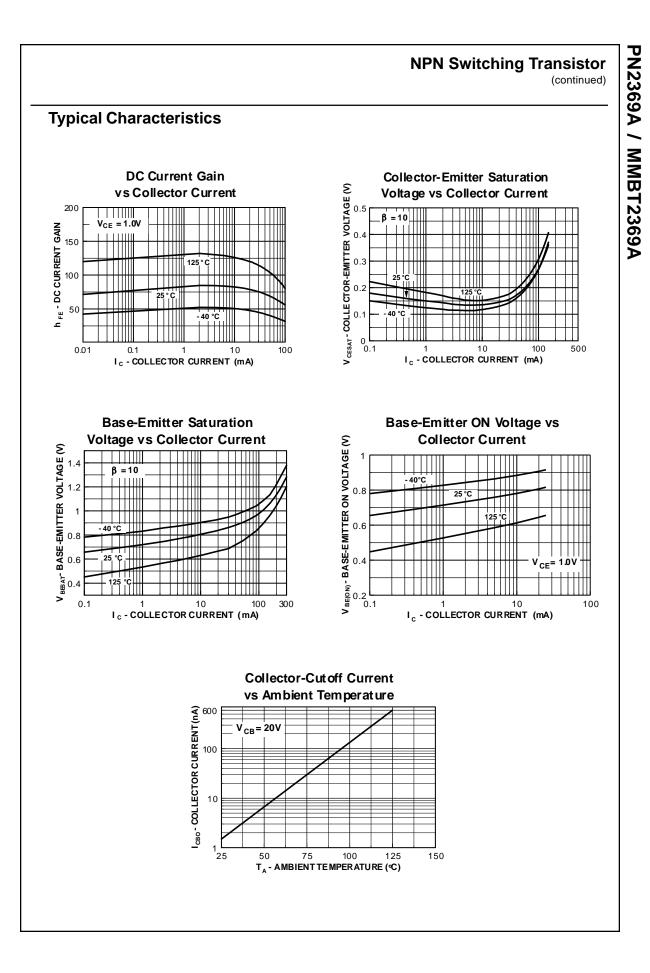
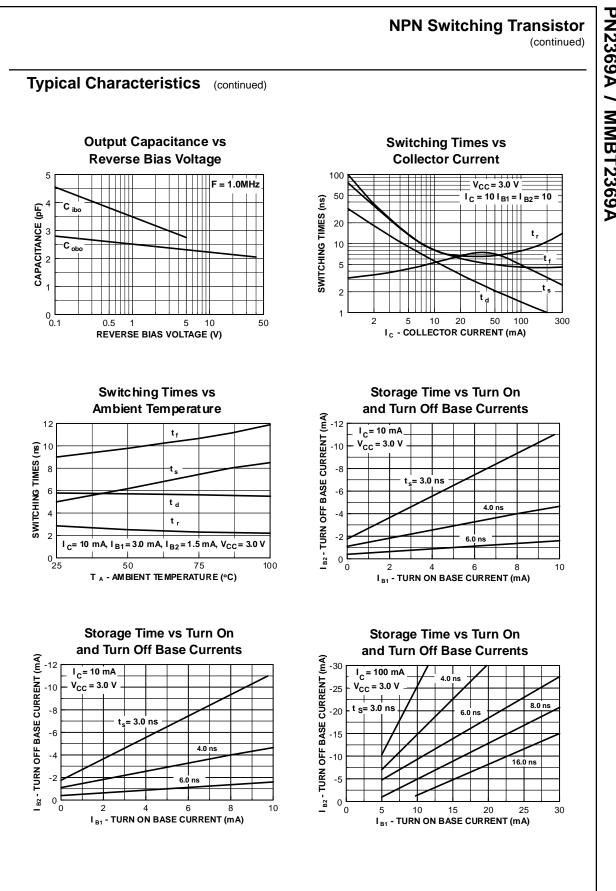
# NPN Switching Transistor (continued)

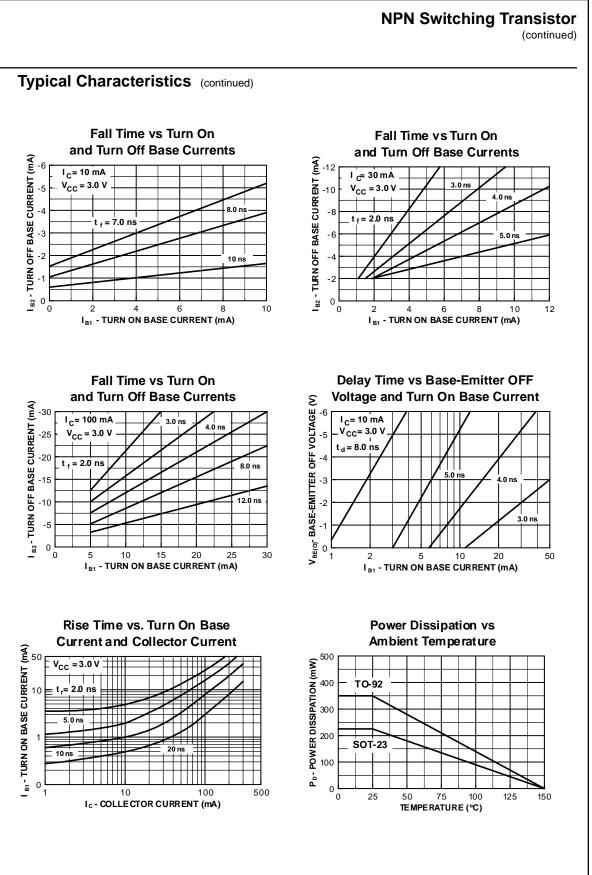
Symbol	Parameter	Test Conditions	Min	Мах	Unit
OFF CHAI	RACTERISTICS				
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage*	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 0$	15		V
V <sub>(BR)CES</sub>	Collector-Emitter Breakdown Voltage	$I_{\rm C} = 10 \mu{\rm A},  V_{\rm BE} = 0$	40		V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	$I_{\rm C} = 10 \mu{\rm A},  I_{\rm E} = 0$	40		V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	$I_{\rm E} = 10 \ \mu {\rm A}, \ I_{\rm C} = 0$	4.5		V
I <sub>CBO</sub>	Collector Cutoff Current	$V_{CB} = 20 \text{ V}, \text{ I}_{E} = 0$	-	0.4	μA
		$V_{CB} = 20 \text{ V}, \text{ I}_{E} = 0, \text{ T}_{A} = 125^{\circ}\text{C}$		30	μA
ON CHAR	ACTERISTICS				
h <sub>FE</sub>	DC Current Gain*	$I_{C} = 10 \text{ mA}, V_{CE} = 1.0 \text{ V}$	40	120	
		$I_C = 10 \text{ mA}, V_{CE} = 0.35 \text{ V}, T_A = -55^{\circ}C$	20		
		$I_{C} = 100 \text{ mA}, V_{CE} = 1.0 \text{ V}$	20	0.0	V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage*	$I_{C} = 10 \text{ mA}, I_{B} = 1.0 \text{ mA}$ $I_{C} = 10 \text{ mA}, I_{B} = 1.0 \text{ mA}, T_{A} = 125^{\circ}\text{C}$		0.2 0.3	
		$I_{\rm C} = 30$ mA, $I_{\rm B} = 3.0$ mA		0.25	v
		$I_{\rm C} = 100 \text{ mA}, I_{\rm B} = 10 \text{ mA}$		0.5	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	$I_{\rm C} = 10$ mA, $I_{\rm B} = 1.0$ mA	0.7	0.85	V
		$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 1.0 \text{ mA}, T_{\rm A} = -55^{\circ}{\rm C}$	0.50	1.02	V V
		$I_{C} = 10 \text{ mA}, I_{B} = 1.0 \text{ mA}, T_{A}= 125^{\circ}\text{C}$ $I_{C} = 30 \text{ mA}, I_{B} = 3.0 \text{ mA}$	0.59	1.15	V
		$I_{\rm C} = 30$ mA, $I_{\rm B} = 3.0$ mA		1.6	v
SMALL SI	GNAL CHARACTERISTICS				
C <sub>obo</sub>	Output Capacitance	$V_{CB} = 5.0 \text{ V}, I_E = 0, f = 1.0 \text{ MHz}$		4.0	pF
Cibo	Input Capacitance	V <sub>EB</sub> = 0.5 V, I <sub>C</sub> = 0, f = 1.0 MHz		5.0	pF
h <sub>fe</sub>	Small-Signal Current Gain	$I_{\rm C} = 10 \text{ mA}, V_{\rm CE} = 10 \text{ V},$	5.0		
		$R_G = 2.0 \text{ k}\Omega, \text{ f} = 100 \text{ MHz}$			
SWITCHI	NG CHARACTERISTICS				
ts	Storage Time	$I_{B1} = I_{B2} = I_{C} = 10 \text{ mA}$		13	ns
t <sub>on</sub>	Turn-On Time	$V_{CC} = 3.0 \text{ V}, I_C = 10 \text{ mA},$ $I_{B1} = 3.0 \text{ mA}$		12	ns
t <sub>off</sub>	Turn-Off Time	$V_{CC} = 3.0 \text{ V}, I_{C} = 10 \text{ mA},$		18	ns
		I <sub>B1</sub> = 3.0 mA, I <sub>B2</sub> = 1.5 mA			_
*Pulse Test:	Pulse Width $\leq$ 300 $\mu s,$ Duty Cycle $\leq$ 2.0%				
Spico	Model				



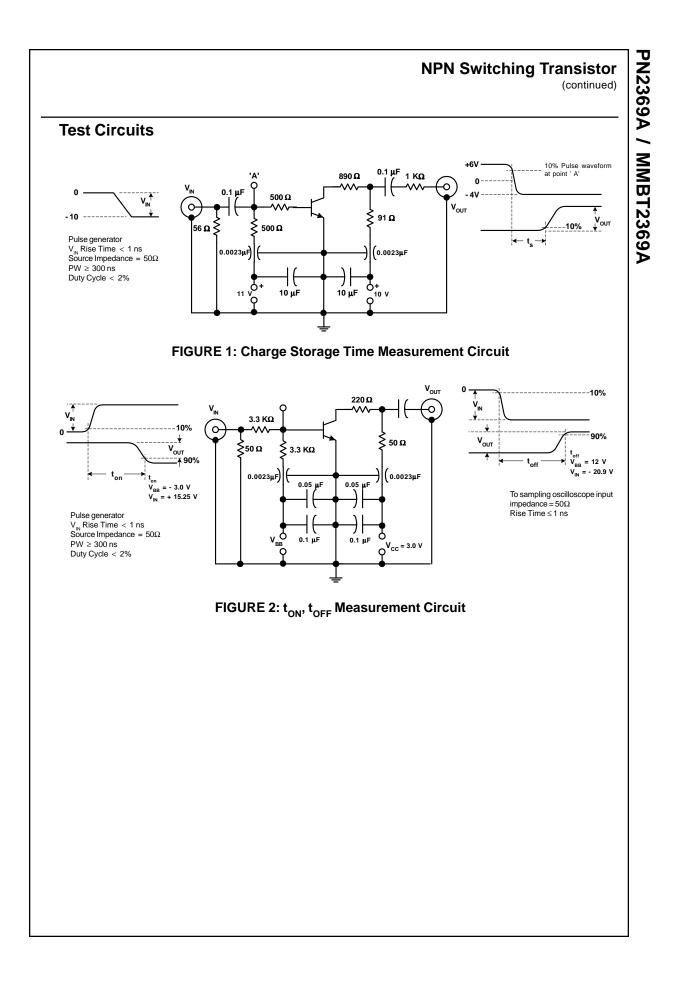
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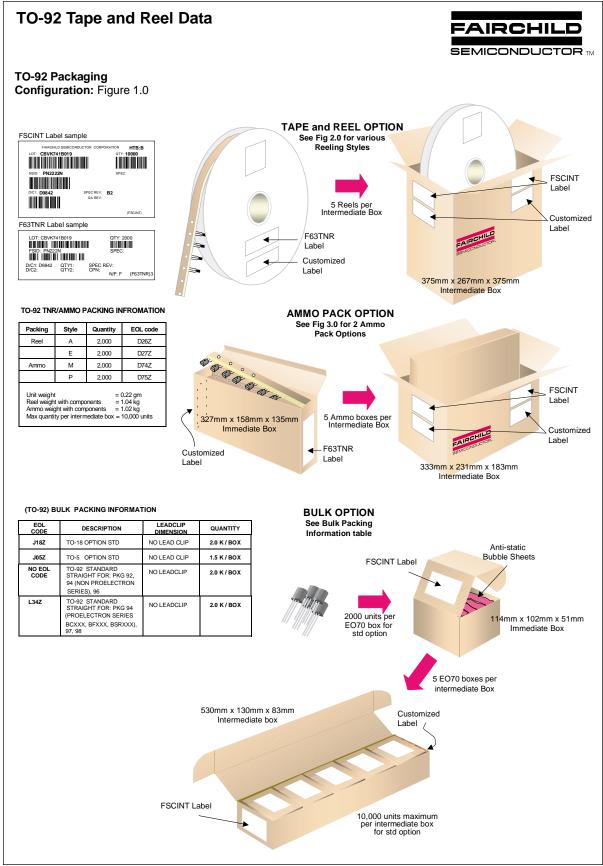


# PN2369A / MMBT2369A



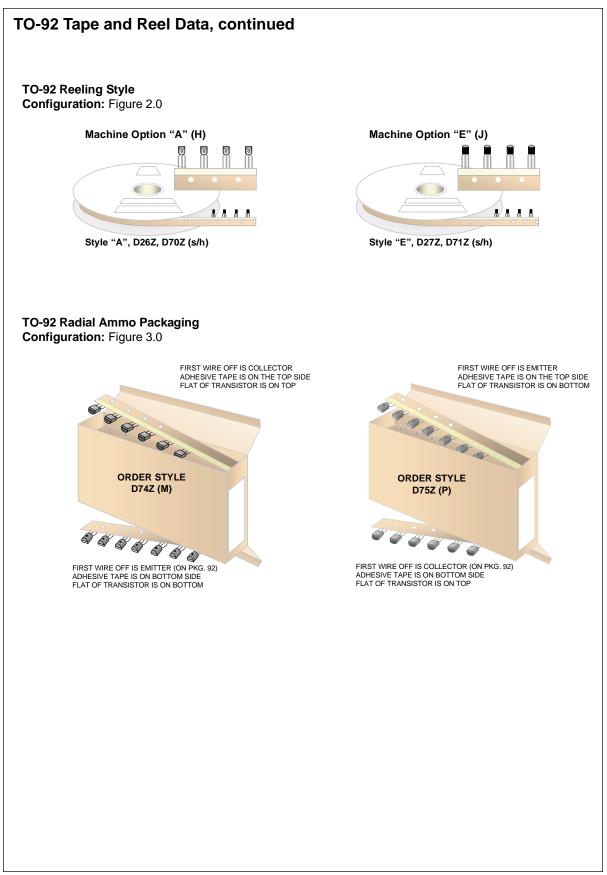
PN2369A / MMBT2369A



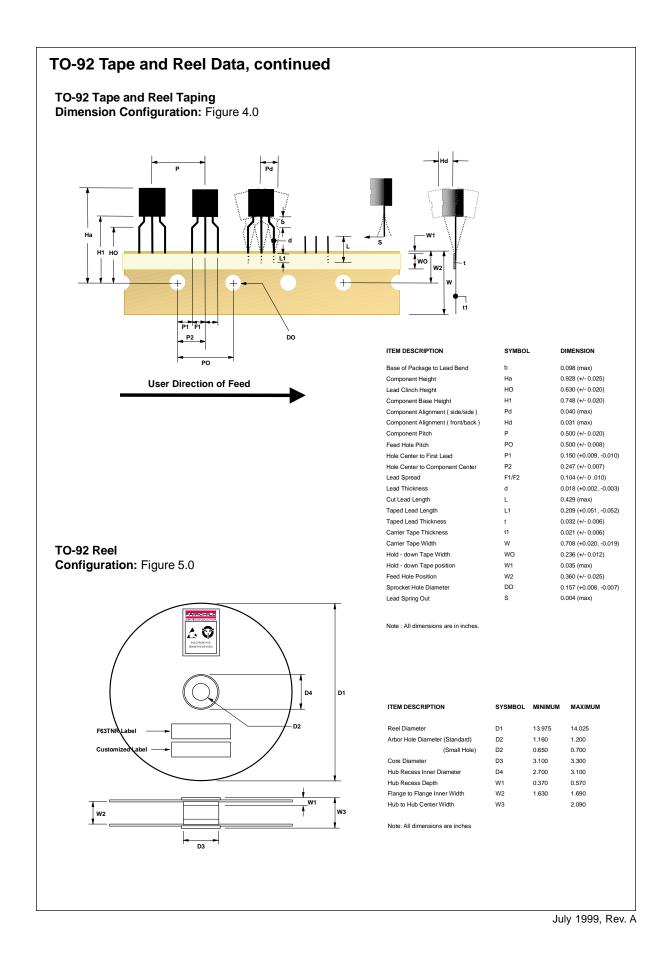


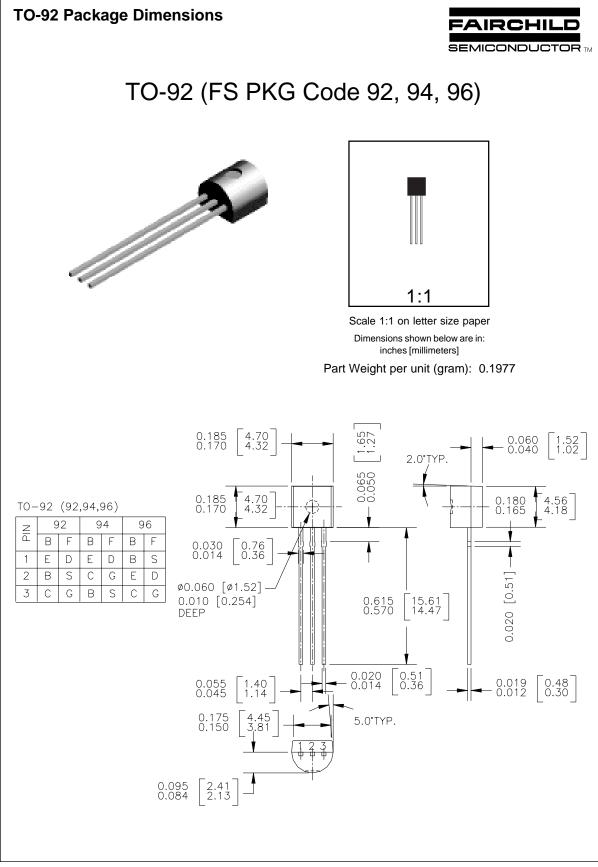
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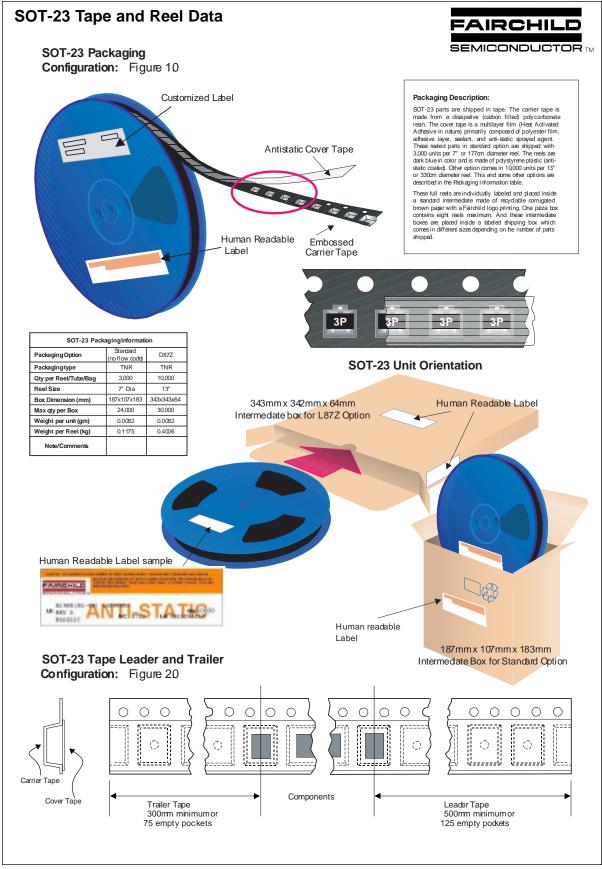
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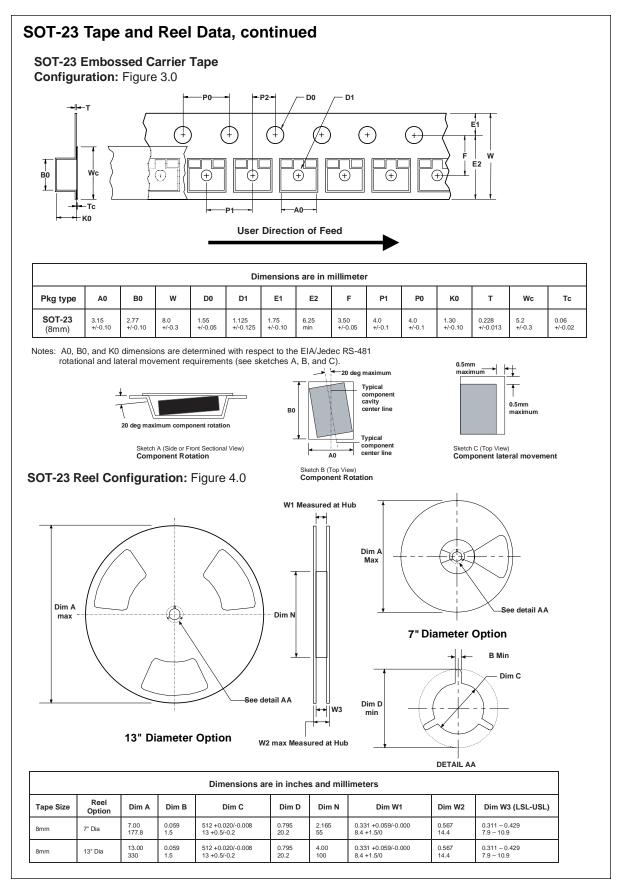
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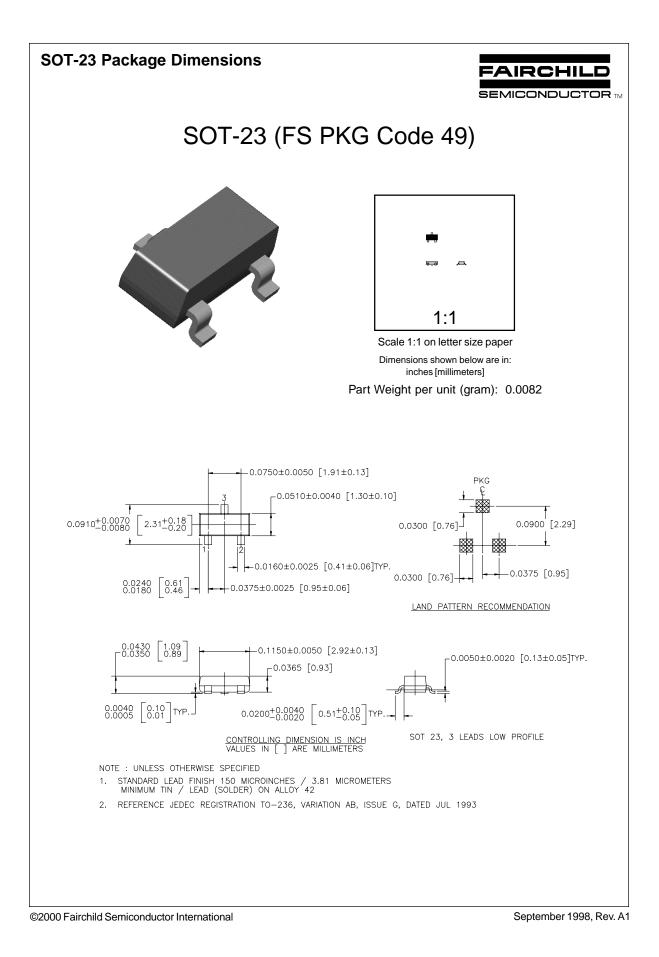


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